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1. General description

Dual Logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- · Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- · Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Limiting value	imiting values FET1 and FET2						
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	21	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	64	W
Static charact	eristics FET1 and FET2				,	,	,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	15.7	21.7	mΩ
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 64 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	8.4	-	nC



Dual N-channel 80 V, 22 m Ω logic level MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4	
8	D1	drain1	LFPAK56D (SOT1205)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9K22-80E	LFPAK56D	plastic, single ended surface mounted package (LFPAK56D); 8 leads; 1.27 mm pitch; 4.7 mm x 5.3 mm x 1.05 mm body	SOT1205		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9K22-80E	92280E

8. Limiting values

Table 5. Limiting values

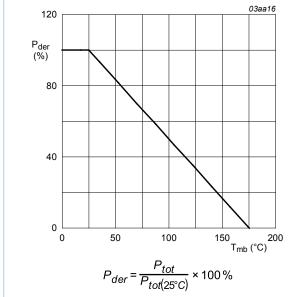
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Limiting values	imiting values FET1 and FET2					
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	80	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1] [2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	64	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	21	Α
		V _{GS} = 5 V; T _{sp} = 100 °C; <u>Fig. 2</u>		-	15	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	84	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode FET1 and FET2					
I _S	source current	T _{mb} = 25 °C		-	21	Α
Ism	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	84	Α
Avalanche r	uggedness FET1 and FET2				,	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 21 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	116	mJ

- [1] [2] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- Significantly longer life times are achieved by lowering T_j and or V_{GS}
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C [3]
- Refer to application note AN10273 for further information



Normalized total power dissipation as a Fig. 1. function of mounting base temperature

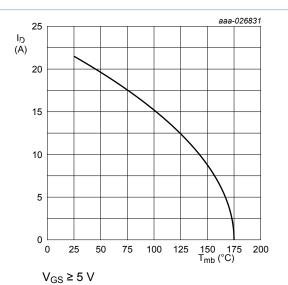
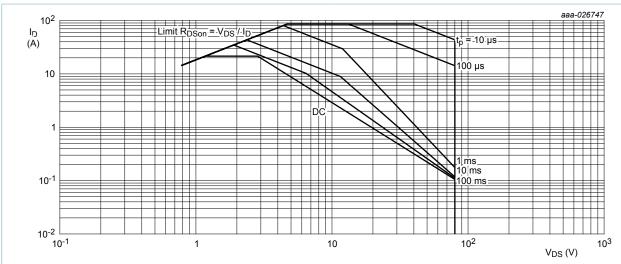


Fig. 2. Continuous drain current as a function of mounting base temperature, FET1 and FET2

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 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET1 and FET2

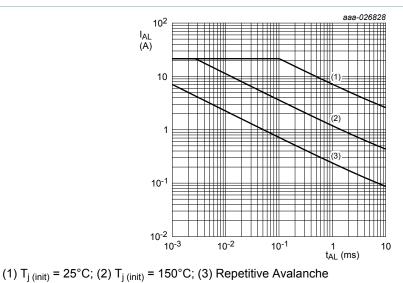


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.36	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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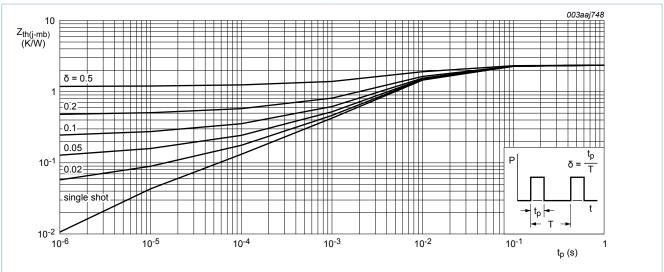


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration, FET1 and FET2

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics FET1 and FET2		,			
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	80	-	-	V
Static character (BR)DSS (GS(th)) DSS GSS RDSon	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9; Fig. 10}$	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.01	1	μΑ
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$	-	15.7	21.7	mΩ
		V_{GS} = 10 V; I_{D} = 10 A; T_{j} = 25 °C; Fig. 11	-	14.4	19	mΩ
		V_{GS} = 5 V; I_D = 10 A; T_j = 175 °C; Fig. 12	-	-	54.5	mΩ
Dynamic ch	aracteristics FET1 and FE	T2	'	'	,	
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$	-	23.1	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	5.4	-	nC
Q_{GD}	gate-drain charge		-	8.4	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2342	3115	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	170	204	pF
C _{rss}	reverse transfer capacitance	V ₂₀ = 60 V: R ₁ = 5 O: V ₂₀ = 5 V:	-	89	122	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 60 \text{ V}; R_{L} = 5 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_{j} = 25 \text{ °C}$	-	13.9	-	ns
t _r	rise time		-	24.9	-	ns
$t_{d(off)}$	turn-off delay time		-	28.6	-	ns
t _f	fall time		-	20.6	-	ns
Source-dra	in diode FET1 and FET2					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	28.4	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	33	-	nC

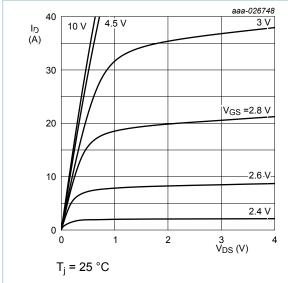


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

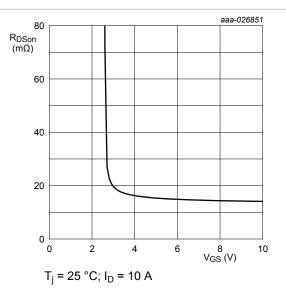


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2

10⁻¹

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003aah026

aaa-026853

4 5 V

V_{GS} = _10_V_

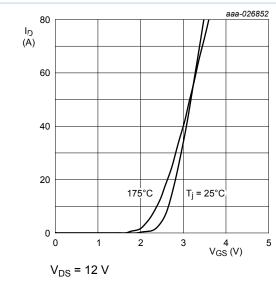
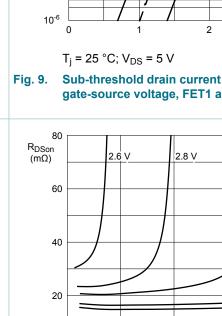


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values, **FET1 and FET2**



0



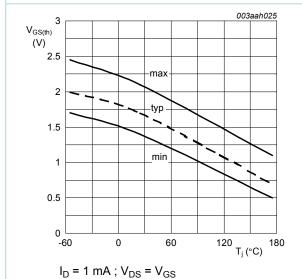
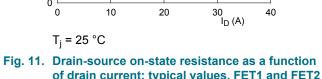


Fig. 10. Gate-source threshold voltage as a function of junction temperature, FET1 and FET2

Fig. 9. Sub-threshold drain current as a function of gate-source voltage, FET1 and FET2



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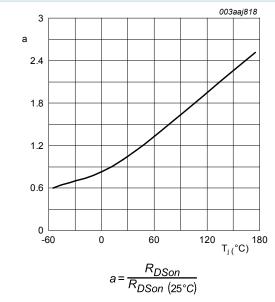


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature, FET1 and FET2

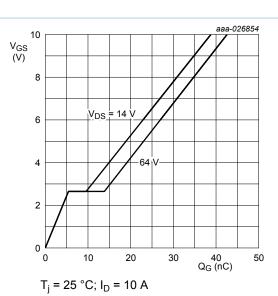


Fig. 13. Gate-source voltage as a function of gate charge; typical values, FET1 and FET2

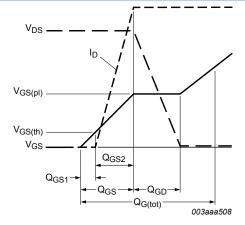


Fig. 14. Gate charge waveform definitions

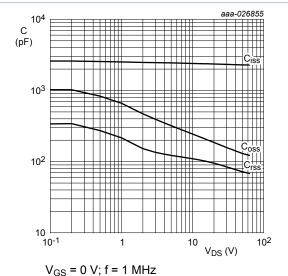
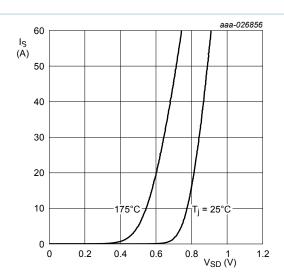


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET1 and FET2

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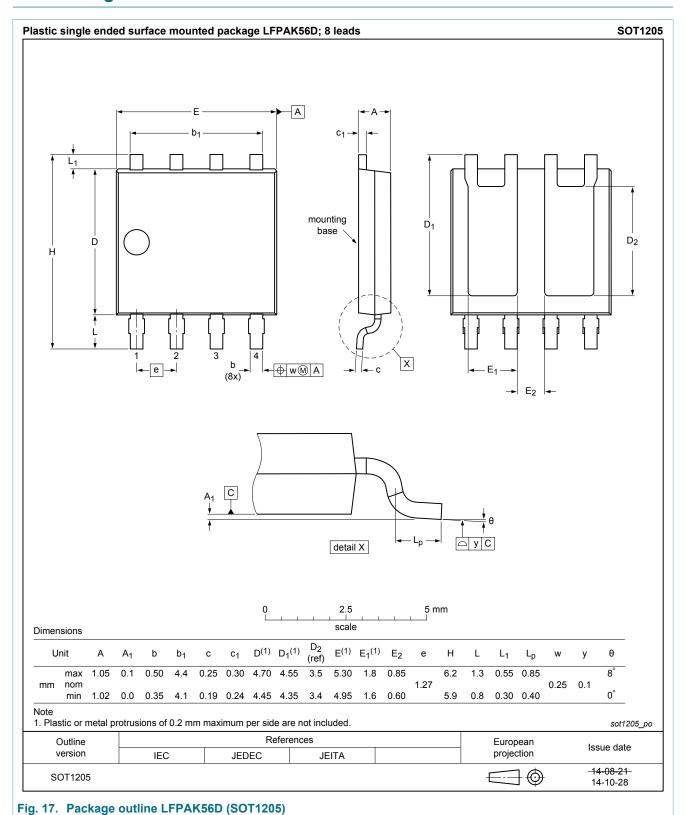


 $V_{GS} = 0 V$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET1 and FET2

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11. Package outline



BUK9K22-80E

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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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